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UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Mitsubishi FUJIKI** Group Art Unit: 2823  
 Application Number: 10/772,253 Examiner: **Thanh V. Pham**  
 Filed: February 6, 2004 Confirmation Number: 6491

For: **METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE  
 INCLUDING A LOW-TEMPERATURE LOWER  
 ELECTRODE FORMING STEP**

Attorney docket Number: 062068  
 Customer Number: 38834

DECLARATION UNDER 37 C.F.R. § 1.132

Commissioner for Patents  
 P.O. Box 4450  
 Alexandria, VA 22313-1450

Date Filed 

Sir:

1. Mitsubishi Fujiki, a citizen of Japan, hereby declare and state the following:

1. I graduated from Osaka University of Osaka, Japan in 1996 with a Ph.D. degree in Science.

2. Since 1997, I have been employed by Fujitsu Limited of Kanagawa, Japan where my present title is engineer of FeRAM development. During my employment therein, I have conducted research and development of processing for FeRAM.

3. I am the author of the following publications:

M. Fujiki et al., Integrated Ferroelectrics, 26, [1-4] 269-279 (1999).

J.S. Cross et al., Jpn. J. Appl. Phys., 38, L446-450 (1999).

4. I have read and am familiar with the above-identified patent application as well as the Official Action dated Aug. 28, 2007, in the application.

5. I have read and am familiar with the contents of cited references, U.S. Patent Nos. 6,300,654 to Coover et al.; 6,444,099 to Sasaki et al.; and 6,964,873 to Matsumoto et al. cited in the Official Actions in the above-identified application.